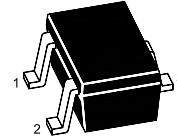
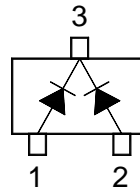


RB715W

SHOTTKY BARRIER DIODE

Application

- Low current rectification



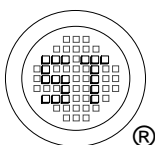
SOT-323 Plastic Package
Marking Code: 3D

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	40	V
Average Rectified Forward Current	$I_{F(AV)}$	30	mA
Peak Forward Surge Current ($t = 8.3\text{ ms}$)	I_{FSM}	200	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$	V_F	-	-	0.37	V
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	40	-	-	V
Reverse Current at $V_R = 10\text{ V}$	I_R	-	-	1	μA
Capacitance between Terminals at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_t	-	2	-	pF

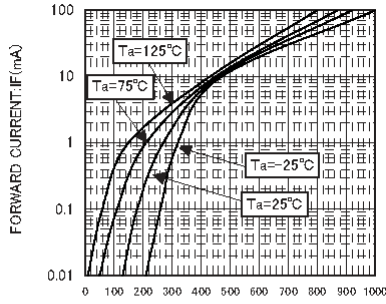


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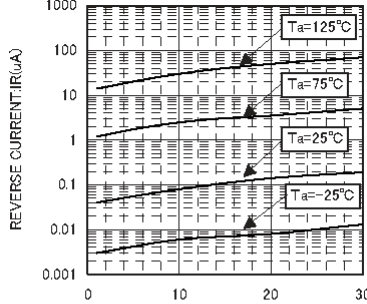


Dated: 13/12/2011 Rev: 01

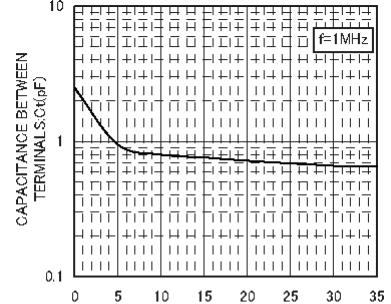
RB715W



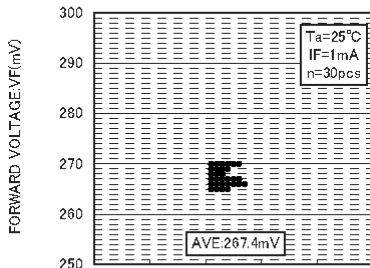
FORWARD VOLTAGE: VF(mV)
VF-IF CHARACTERISTICS



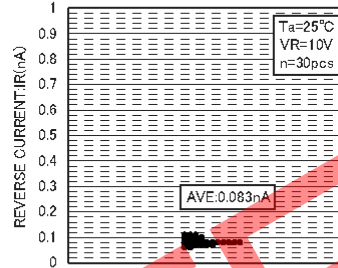
REVERSE VOLTAGE: VR(V)
VR-IR CHARACTERISTICS



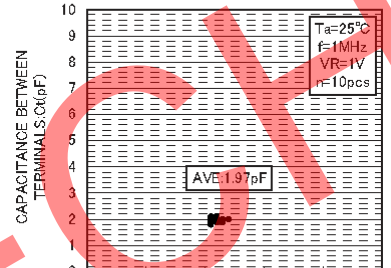
REVERSE VOLTAGE: VR(V)
VR-Ct CHARACTERISTICS



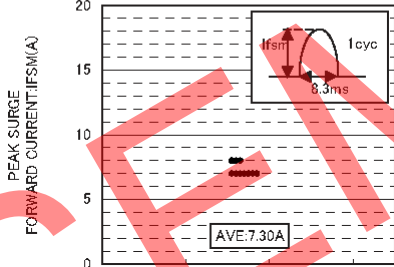
VF DISPERSION MAP



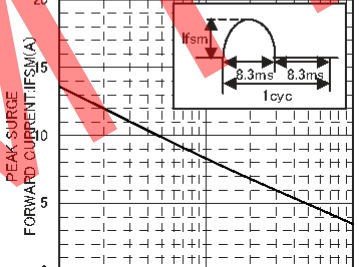
IR DISPERSION MAP



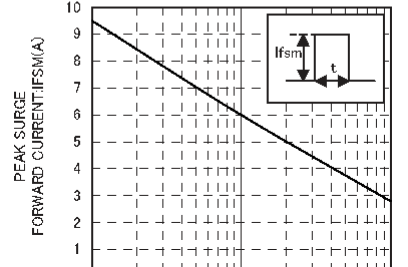
Ct DISPERSION MAP



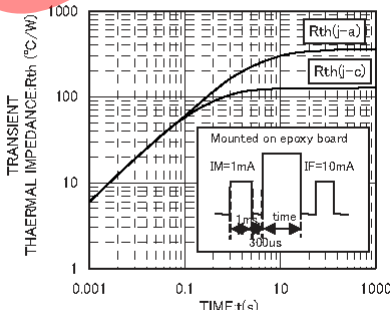
IFSM DISPERSION MAP



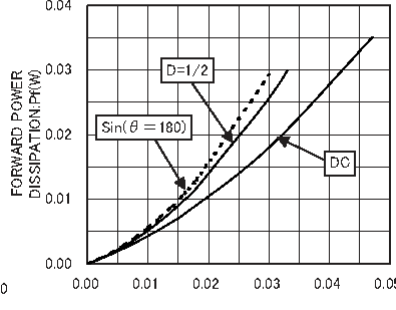
IFSM-CYCLE CHARACTERISTICS



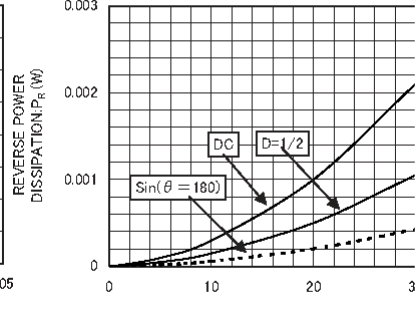
IFSM-t CHARACTERISTICS



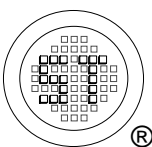
Rth-t CHARACTERISTICS



AVERAGE RECTIFIED FORWARD CURRENT Io(A)
Io-Pf CHARACTERISTICS



REVERSE VOLTAGE: VR(V)
VR-Pf CHARACTERISTICS



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